

AMENDMENTS TO THE SPECIFICATION

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

Please amend the first full paragraph on page 16 as follows:

FIG. 4 is a longitudinal sectional view of the oscillation element 34-1 of FIG. 3. As shown in FIG. 4, the oscillation element 34-1 is formed by a substrate 40, a frame body 42 formed on the surface of the object side of the substrate 40, a film body 44 disposed by closing the aperture of the frame body 42, etc. The substrate 40, the frame body 42, and the film body 44 are formed by including a semiconductor compound (for example, a silicon compound). An internal space 48 is partitioned by the frame body 42 and the film body 44. The internal space 48 is kept in a state having a predetermined degree of vacuum or a state of being filled up with a predetermined gas. Also, the oscillation element 34-1 has an electrode 35-1 disposed on the surface of the back face side of the substrate 40 and an electrode 35-2 disposed on the surface of the object side of the film body 44. The electrode 35-1 is connected to a drive-signal power source 50 of the transmitting means 12 through a connection terminal 49-1. The electrode 35-2 is connected to a direct-current bias power source 51 of the bias means 14 through a connection terminal 49-2.

Please amend the first full paragraph on page 21 as follows:

The switching means 53 is provided corresponding to the number of the sections P1 to PA. Accordingly, the value of the direct-current bias applied to the electrode of each of the sections P1 to PA is adjusted by the number of closings of

the switches 53-1 to 53-n of each switching means 53. For example, for the section P1 located at the end of the transducer 55 in the minor-axis direction Y, a bias voltage V_a is applied by turning only the switch 53-1 on. For the section P ($A/2$) located at the center of the transducer 55 in the minor-axis direction Y, a bias voltage ($V_a \cdot n$) is applied to the electrode by turning all the switches 53-1 to ~~72-n on~~53-n on. In this manner, by changing the number of switches 53-1 to ~~72-n to~~53-n to be turned on in each switching means 53, it is possible to make the bias voltage to be applied to each section of the transducer 55 different for each section.